

**MOSFET WITH RAISED STI ISOLATION SELF-ALIGNED TO THE GATE STACK
ABSTRACT**

A semiconductor structure comprising a transistor (39) having a gate conductor (16) that has first and second edges bounded by raised isolation structures (e.g. STI) (30). A source diffusion (38) is self-aligned to the third edge and a drain diffusion (38) is self-aligned to the fourth edge of the gate electrode.

Fig. 8